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### Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	376
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/intel/ep20k200efc672-2x">https://www.e-xfl.com/product-detail/intel/ep20k200efc672-2x</a>

## Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack<sup>®</sup> Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires.

Figure 1 shows an overview of the APEX 20K device.

**Figure 1. APEX 20K Device Block Diagram**

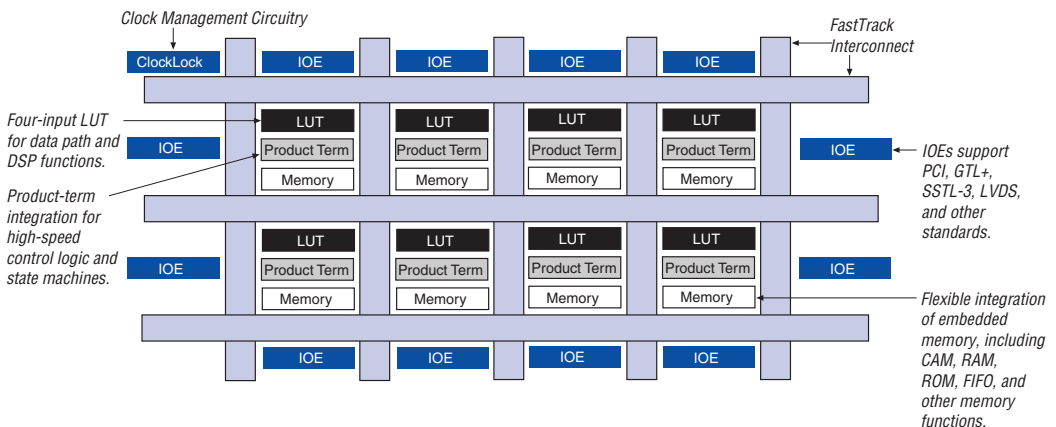


Figure 12. APEX 20KE FastRow Interconnect

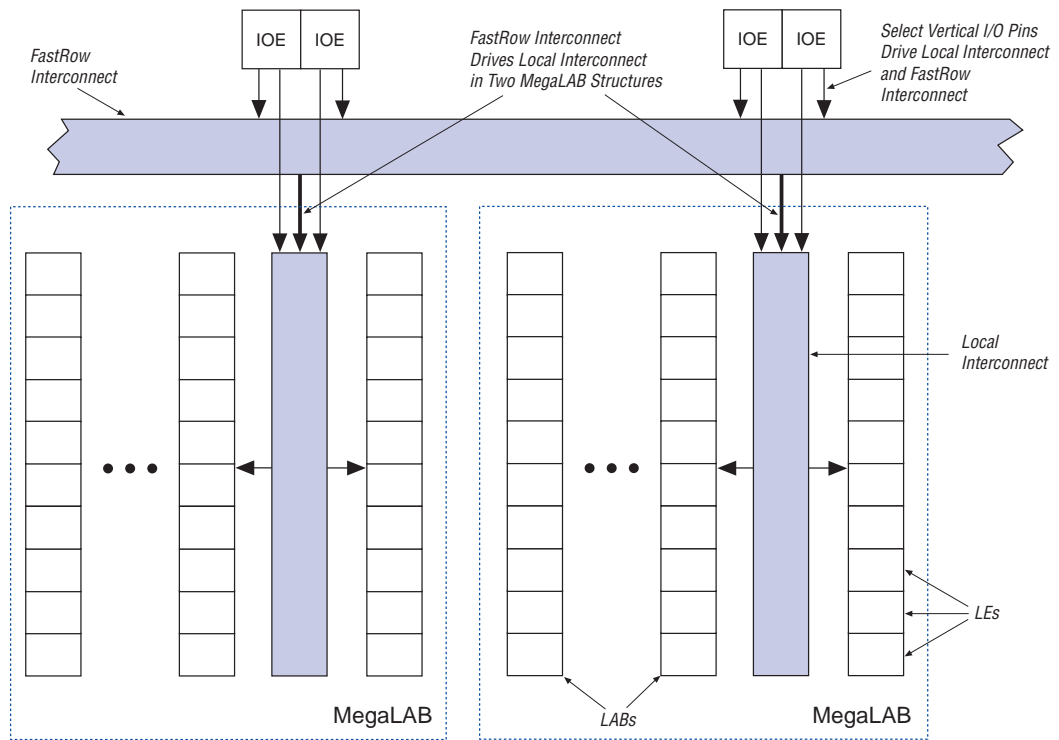
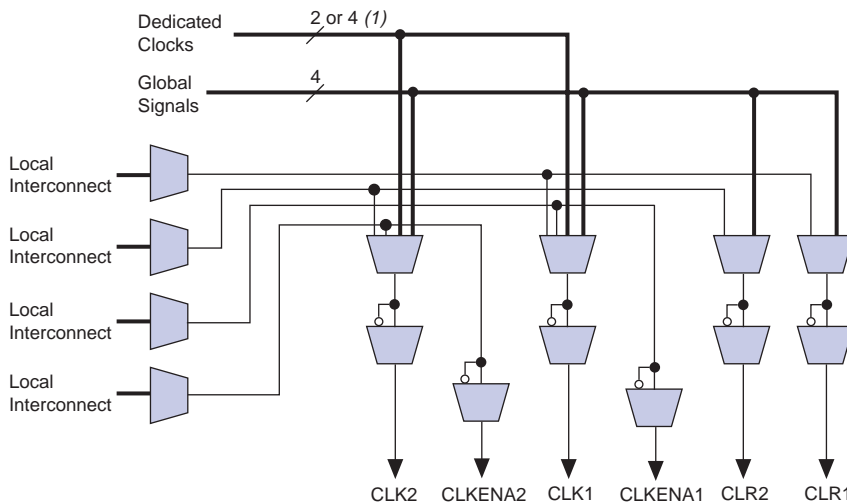


Table 9 summarizes how various elements of the APEX 20K architecture drive each other.

The programmable register also supports an asynchronous clear function. Within the ESB, two asynchronous clears are generated from global signals and the local interconnect. Each macrocell can either choose between the two asynchronous clear signals or choose to not be cleared. Either of the two clear signals can be inverted within the ESB. Figure 15 shows the ESB control logic when implementing product-terms.

**Figure 15. ESB Product-Term Mode Control Logic**



**Note to Figure 15:**

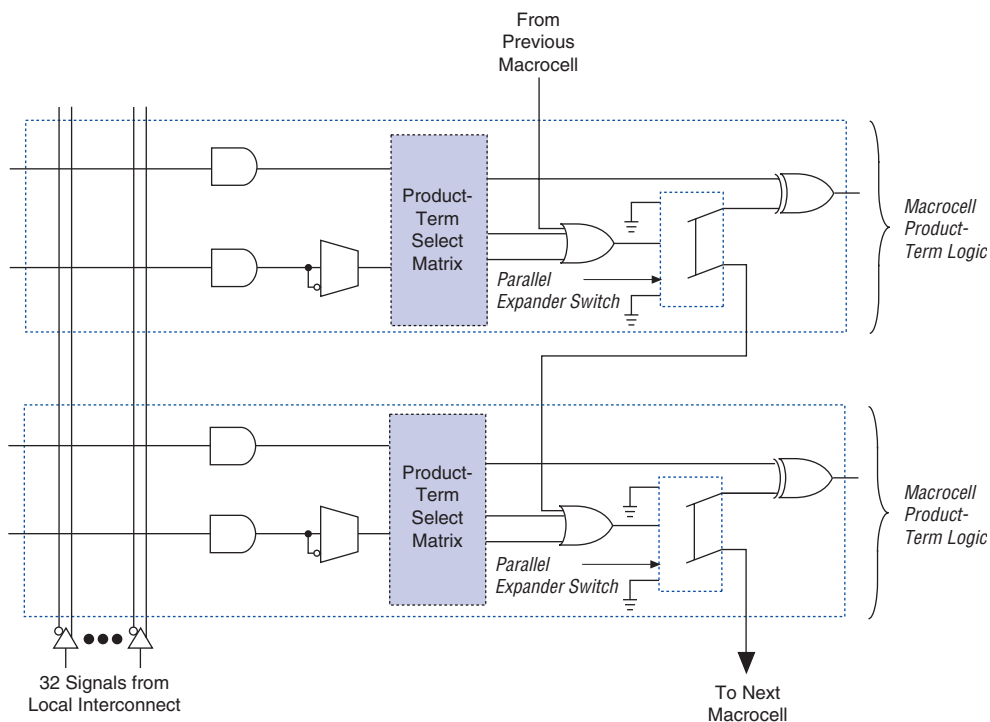
(1) APEX 20KE devices have four dedicated clocks.

### Parallel Expanders

Parallel expanders are unused product terms that can be allocated to a neighboring macrocell to implement fast, complex logic functions. Parallel expanders allow up to 32 product terms to feed the macrocell OR logic directly, with two product terms provided by the macrocell and 30 parallel expanders provided by the neighboring macrocells in the ESB.

The Quartus II software Compiler can allocate up to 15 sets of up to two parallel expanders per set to the macrocells automatically. Each set of two parallel expanders incurs a small, incremental timing delay. Figure 16 shows the APEX 20K parallel expanders.

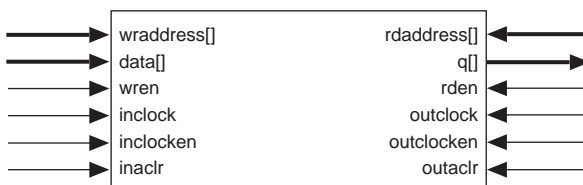
**Figure 16. APEX 20K Parallel Expanders**



## Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

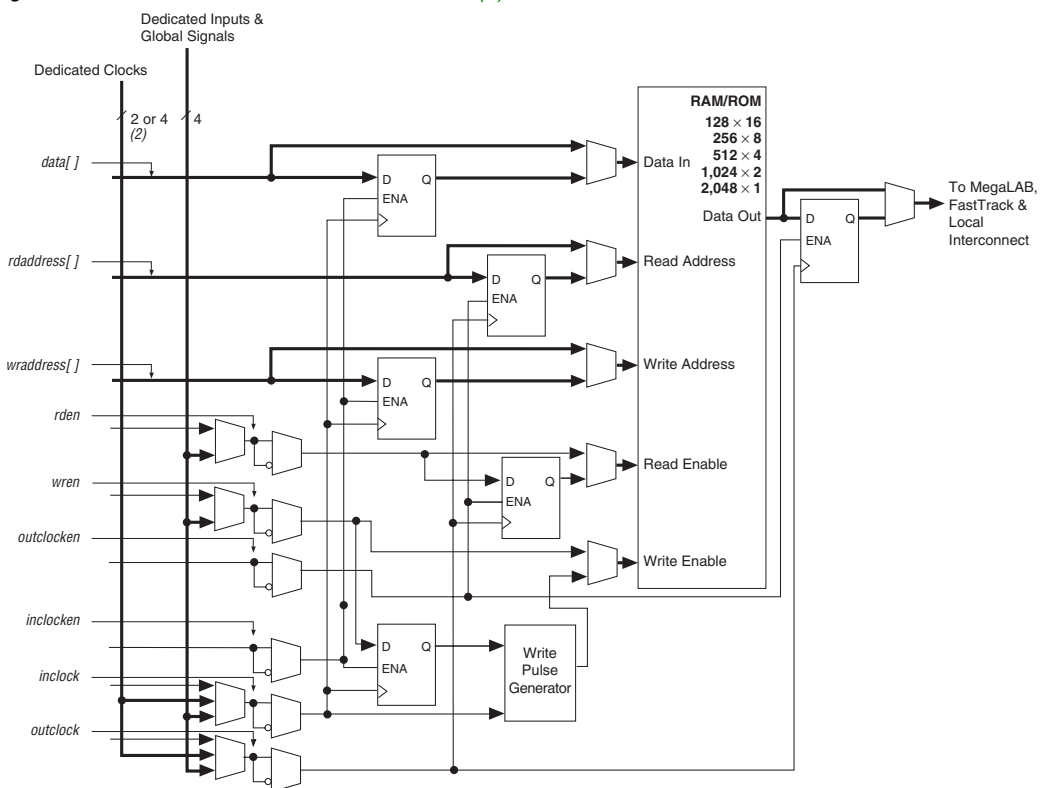
**Figure 17. ESB Block Diagram**



## Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

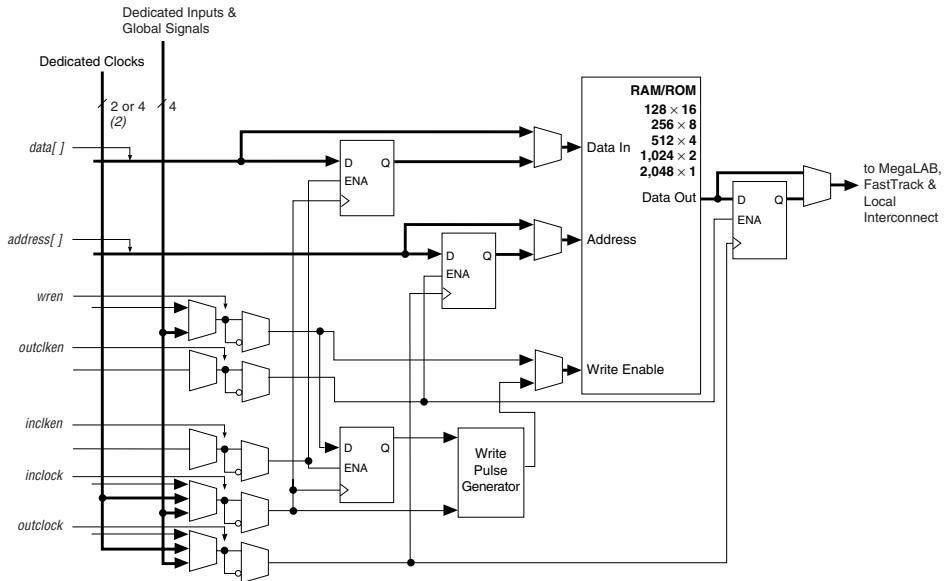
**Figure 20. ESB in Read/Write Clock Mode** *Note (1)*



### Notes to Figure 20:

- (1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
- (2) APEX 20KE devices have four dedicated clocks.

Figure 22. ESB in Single-Port Mode *Note (1)*



**Notes to Figure 22:**

- (1) All registers can be asynchronously cleared by ESB local interconnect signals, global signals, or the chip-wide reset.
- (2) APEX 20KE devices have four dedicated clocks.

**Content-Addressable Memory**

In APEX 20KE devices, the ESB can implement CAM. CAM can be thought of as the inverse of RAM. When read, RAM outputs the data for a given address. Conversely, CAM outputs an address for a given data word. For example, if the data FA12 is stored in address 14, the CAM outputs 14 when FA12 is driven into it.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

Table 10 describes the APEX 20K programmable delays and their logic options in the Quartus II software.

<b>Table 10. APEX 20K Programmable Delay Chains</b>	
<b>Programmable Delays</b>	<b>Quartus II Logic Option</b>
Input pin to core delay	Decrease input delay to internal cells
Input pin to input register delay	Decrease input delay to input register
Core to output register delay	Decrease input delay to output register
Output register $t_{CO}$ delay	Increase delay to output pin

The Quartus II software compiler can program these delays automatically to minimize setup time while providing a zero hold time. Figure 25 shows how fast bidirectional I/Os are implemented in APEX 20K devices.

The register in the APEX 20K IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, the register cannot be asynchronously cleared or preset. This feature is useful for cases where the APEX 20K device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.



APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

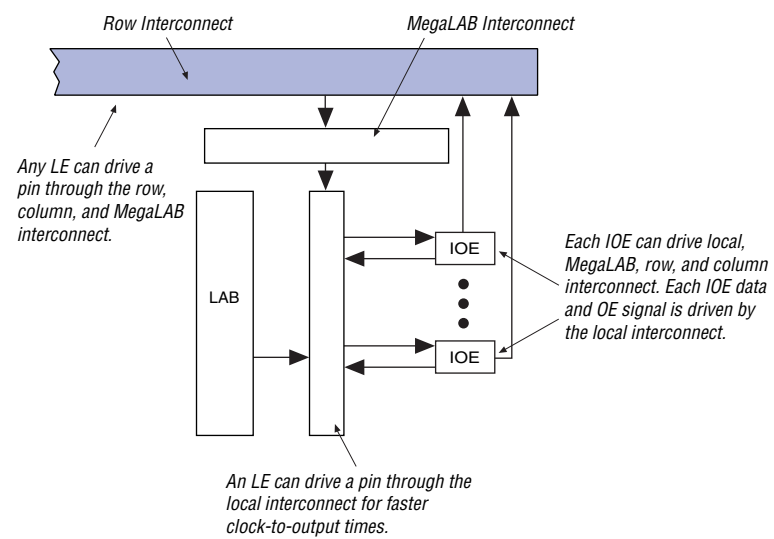
**Table 11** describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

<b>Table 11. APEX 20KE Programmable Delay Chains</b>	
<b>Programmable Delays</b>	<b>Quartus II Logic Option</b>
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register $t_{CO}$ Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. **Figure 26** shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. **Figure 27** shows how a row IOE connects to the interconnect.

**Figure 27. Row IOE Connection to the Interconnect**



**Notes to Table 16:**

- (1) To implement the ClockLock and ClockBoost circuitry with the Quartus II software, designers must specify the input frequency. The Quartus II software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The  $f_{CLKDEV}$  parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.
- (2) Twenty-five thousand parts per million (PPM) equates to 2.5% of input clock period.
- (3) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration because the  $t_{LOCK}$  value is less than the time required for configuration.
- (4) The  $t_{JITTER}$  specification is measured under long-term observation.

Tables 17 and 18 summarize the ClockLock and ClockBoost parameters for APEX 20KE devices.

<b>Table 17. APEX 20KE ClockLock &amp; ClockBoost Parameters</b> <i>Note (1)</i>						
<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>
$t_R$	Input rise time				5	ns
$t_F$	Input fall time				5	ns
$t_{INDUTY}$	Input duty cycle		40		60	%
$t_{INJITTER}$	Input jitter peak-to-peak				2% of input period	peak-to-peak
$t_{OUTJITTER}$	Jitter on ClockLock or ClockBoost-generated clock				0.35% of output period	RMS
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		45		55	%
$t_{LOCK}$ (2), (3)	Time required for ClockLock or ClockBoost to acquire lock				40	μs

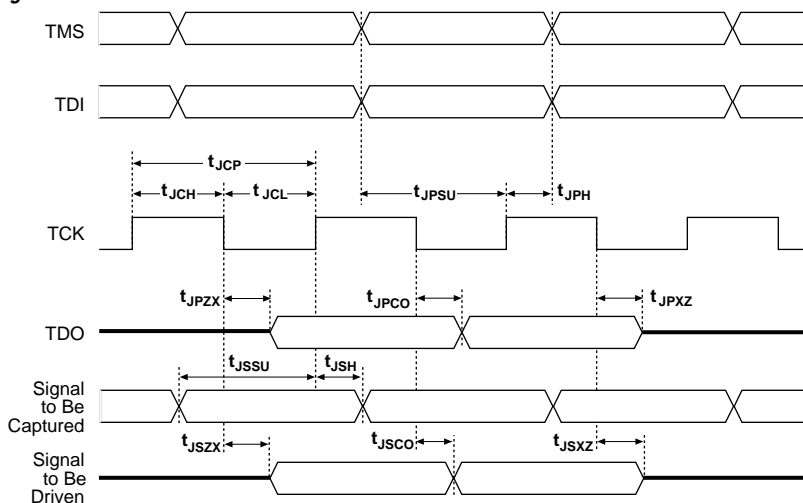
**Table 21. 32-Bit APEX 20K Device IDCODE**

Device	IDCODE (32 Bits) <sup>(1)</sup>			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) <sup>(2)</sup>
EP20K30E	0000	1000 0000 0011 0000	000 0110 1110	1
EP20K60E	0000	1000 0000 0110 0000	000 0110 1110	1
EP20K100	0000	0000 0100 0001 0110	000 0110 1110	1
EP20K100E	0000	1000 0001 0000 0000	000 0110 1110	1
EP20K160E	0000	1000 0001 0110 0000	000 0110 1110	1
EP20K200	0000	0000 1000 0011 0010	000 0110 1110	1
EP20K200E	0000	1000 0010 0000 0000	000 0110 1110	1
EP20K300E	0000	1000 0011 0000 0000	000 0110 1110	1
EP20K400	0000	0001 0110 0110 0100	000 0110 1110	1
EP20K400E	0000	1000 0100 0000 0000	000 0110 1110	1
EP20K600E	0000	1000 0110 0000 0000	000 0110 1110	1
EP20K1000E	0000	1001 0000 0000 0000	000 0110 1110	1

**Notes to Table 21:**

- (1) The most significant bit (MSB) is on the left.  
 (2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

**Figure 31. APEX 20K JTAG Waveforms**

**Table 29. APEX 20KE Device DC Operating Conditions** *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IH}$	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, $0.5 \times V_{CCIO}$ (10)		4.1	V
$V_{IL}$	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		-0.5		$0.8, 0.3 \times V_{CCIO}$ (10)	V
$V_{OH}$	3.3-V high-level LVTTL output voltage	$I_{OH} = -12$ mA DC, $V_{CCIO} = 3.00$ V (11)	2.4			V
	3.3-V high-level LVCMOS output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 3.00$ V (11)	$V_{CCIO} - 0.2$			V
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5$ mA DC, $V_{CCIO} = 3.00$ to $3.60$ V (11)	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 2.30$ V (11)	2.1			V
		$I_{OH} = -1$ mA DC, $V_{CCIO} = 2.30$ V (11)	2.0			V
		$I_{OH} = -2$ mA DC, $V_{CCIO} = 2.30$ V (11)	1.7			V
$V_{OL}$	3.3-V low-level LVTTL output voltage	$I_{OL} = 12$ mA DC, $V_{CCIO} = 3.00$ V (12)			0.4	V
	3.3-V low-level LVCMOS output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 3.00$ V (12)			0.2	V
	3.3-V low-level PCI output voltage	$I_{OL} = 1.5$ mA DC, $V_{CCIO} = 3.00$ to $3.60$ V (12)			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.2	V
		$I_{OL} = 1$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.4	V
		$I_{OL} = 2$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.7	V
$I_I$	Input pin leakage current	$V_I = 4.1$ to $-0.5$ V (13)	-10		10	$\mu$ A
$I_{OZ}$	Tri-stated I/O pin leakage current	$V_O = 4.1$ to $-0.5$ V (13)	-10		10	$\mu$ A
$I_{CC0}$	$V_{CC}$ supply current (standby) (All ESBs in power-down mode)	$V_I =$ ground, no load, no toggling inputs, -1 speed grade		10		mA
		$V_I =$ ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
$R_{CONF}$	Value of I/O pin pull-up resistor before and during configuration	$V_{CCIO} = 3.0$ V (14)	20		50	k $\Omega$
		$V_{CCIO} = 2.375$ V (14)	30		80	k $\Omega$
		$V_{CCIO} = 1.71$ V (14)	60		150	k $\Omega$

Tables 40 through 42 show the  $f_{MAX}$  timing parameters for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

**Table 40. EP20K100  $f_{MAX}$  Timing Parameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
$t_{SU}$	0.5		0.6		0.8		ns
$t_H$	0.7		0.8		1.0		ns
$t_{CO}$		0.3		0.4		0.5	ns
$t_{LUT}$		0.8		1.0		1.3	ns
$t_{ESBRC}$		1.7		2.1		2.4	ns
$t_{ESBWC}$		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
$t_{ESBDD}$		2.5		3.3		3.6	ns
$t_{PD}$		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.6		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
$t_{F1-4}$		0.5		0.6		0.7	ns
$t_{F5-20}$		1.6		1.7		1.8	ns
$t_{F20+}$		2.2		2.2		2.3	ns
$t_{CH}$	2.0		2.5		3.0		ns
$t_{CL}$	2.0		2.5		3.0		ns
$t_{CLRP}$	0.3		0.4		0.4		ns
$t_{PREP}$	0.5		0.5		0.5		ns
$t_{ESBCH}$	2.0		2.5		3.0		ns
$t_{ESBCL}$	2.0		2.5		3.0		ns
$t_{ESBWP}$	1.6		1.9		2.2		ns
$t_{ESBRP}$	1.0		1.3		1.4		ns

**Table 56. EP20K60E  $t_{MAX}$  ESB Timing Microparameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{ESBARC}$		1.83		2.57		3.79	ns
$t_{ESBSRC}$		2.46		3.26		4.61	ns
$t_{ESBAWC}$		3.50		4.90		7.23	ns
$t_{ESBSWC}$		3.77		4.90		6.79	ns
$t_{ESBWASU}$	1.59		2.23		3.29		ns
$t_{ESBWAH}$	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.75		2.46		3.62		ns
$t_{ESBWDH}$	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.76		2.47		3.64		ns
$t_{ESBRAH}$	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.68		2.49		3.87		ns
$t_{ESBWEH}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.08		0.43		1.04		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.29		0.72		1.46		ns
$t_{ESBRADDRSU}$	0.36		0.81		1.58		ns
$t_{ESBDATACO1}$		1.06		1.24		1.55	ns
$t_{ESBDATACO2}$		2.39		3.35		4.94	ns
$t_{ESBDD}$		3.50		4.90		7.23	ns
$t_{PD}$		1.72		2.41		3.56	ns
$t_{PTERMSU}$	0.99		1.56		2.55		ns
$t_{PTERMCO}$		1.07		1.26		1.08	ns

**Table 64. EP20K100E Minimum Pulse Width Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>CH</sub>	2.00		2.00		2.00		ns
t <sub>CL</sub>	2.00		2.00		2.00		ns
t <sub>CLRP</sub>	0.20		0.20		0.20		ns
t <sub>PREP</sub>	0.20		0.20		0.20		ns
t <sub>ESBCH</sub>	2.00		2.00		2.00		ns
t <sub>ESBCL</sub>	2.00		2.00		2.00		ns
t <sub>ESBWP</sub>	1.29		1.53		1.66		ns
t <sub>ESBRP</sub>	1.11		1.29		1.41		ns

**Table 65. EP20K100E External Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>INSU</sub>	2.23		2.32		2.43		ns
t <sub>INH</sub>	0.00		0.00		0.00		ns
t <sub>OUTCO</sub>	2.00	4.86	2.00	5.35	2.00	5.84	ns
t <sub>INSUPLL</sub>	1.58		1.66		-		ns
t <sub>INHPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOPLL</sub>	0.50	2.96	0.50	3.29	-	-	ns

**Table 66. EP20K100E External Bidirectional Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>INSUBIDIR</sub>	2.74		2.96		3.19		ns
t <sub>INHBIDIR</sub>	0.00		0.00		0.00		ns
t <sub>OUTCOBIDIR</sub>	2.00	4.86	2.00	5.35	2.00	5.84	ns
t <sub>XZBIDIR</sub>		5.00		5.48		5.89	ns
t <sub>ZXBIDIR</sub>		5.00		5.48		5.89	ns
t <sub>INSUBIDIRPLL</sub>	4.64		5.03		-		ns
t <sub>INHBIDIRPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOBIDIRPLL</sub>	0.50	2.96	0.50	3.29	-	-	ns
t <sub>XZBIDIRPLL</sub>		3.10		3.42		-	ns
t <sub>ZXBIDIRPLL</sub>		3.10		3.42		-	ns



**Table 68. EP20K160E  $t_{MAX}$  ESB Timing Microparameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{ESBARC}$		1.65		2.02		2.11	ns
$t_{ESBSRC}$		2.21		2.70		3.11	ns
$t_{ESBAWC}$		3.04		3.79		4.42	ns
$t_{ESBSWC}$		2.81		3.56		4.10	ns
$t_{ESBWASU}$	0.54		0.66		0.73		ns
$t_{ESBWAH}$	0.36		0.45		0.47		ns
$t_{ESBWDSU}$	0.68		0.81		0.94		ns
$t_{ESBWDH}$	0.36		0.45		0.47		ns
$t_{ESBRASU}$	1.58		1.87		2.06		ns
$t_{ESBRAH}$	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.41		1.71		2.00		ns
$t_{ESBWEH}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.02		-0.03		0.09		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.14		0.17		0.35		ns
$t_{ESBRADDRSU}$	0.21		0.27		0.43		ns
$t_{ESBDATACO1}$		1.04		1.30		1.46	ns
$t_{ESBDATACO2}$		2.15		2.70		3.16	ns
$t_{ESBDD}$		2.69		3.35		3.97	ns
$t_{PD}$		1.55		1.93		2.29	ns
$t_{PTERMSU}$	1.01		1.23		1.52		ns
$t_{PTERMCO}$		1.06		1.32		1.04	ns

**Table 82. EP20K300E Minimum Pulse Width Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>CH</sub>	1.25		1.43		1.67		ns
t <sub>CL</sub>	1.25		1.43		1.67		ns
t <sub>CLRP</sub>	0.19		0.26		0.35		ns
t <sub>PREP</sub>	0.19		0.26		0.35		ns
t <sub>ESBCH</sub>	1.25		1.43		1.67		ns
t <sub>ESBCL</sub>	1.25		1.43		1.67		ns
t <sub>ESBWP</sub>	1.25		1.71		2.28		ns
t <sub>ESBRP</sub>	1.01		1.38		1.84		ns

**Table 83. EP20K300E External Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>INSU</sub>	2.31		2.44		2.57		ns
t <sub>INH</sub>	0.00		0.00		0.00		ns
t <sub>OUTCO</sub>	2.00	5.29	2.00	5.82	2.00	6.24	ns
t <sub>INSUPLL</sub>	1.76		1.85		-		ns
t <sub>INHPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOPLL</sub>	0.50	2.65	0.50	2.95	-	-	ns

**Table 84. EP20K300E External Bidirectional Timing Parameters**

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t <sub>INSUBIDIR</sub>	2.77		2.85		3.11		ns
t <sub>INHBIDIR</sub>	0.00		0.00		0.00		ns
t <sub>OUTCOBIDIR</sub>	2.00	5.29	2.00	5.82	2.00	6.24	ns
t <sub>XZBIDIR</sub>		7.59		8.30		9.09	ns
t <sub>ZXBIDIR</sub>		7.59		8.30		9.09	ns
t <sub>INSUBIDIRPLL</sub>	2.50		2.76		-		ns
t <sub>INHBIDIRPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOBIDIRPLL</sub>	0.50	2.65	0.50	2.95	-	-	ns
t <sub>XZBIDIRPLL</sub>		5.00		5.43		-	ns
t <sub>ZXBIDIRPLL</sub>		5.00		5.43		-	ns

**Table 92. EP20K600E  $t_{MAX}$  ESB Timing Microparameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{ESBARC}$		1.67		2.39		3.11	ns
$t_{ESBSRC}$		2.27		3.07		3.86	ns
$t_{ESBAWC}$		3.19		4.56		5.93	ns
$t_{ESBSWC}$		3.51		4.62		5.72	ns
$t_{ESBWASU}$	1.46		2.08		2.70		ns
$t_{ESBWAH}$	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.60		2.29		2.97		ns
$t_{ESBWDH}$	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.61		2.30		2.99		ns
$t_{ESBRAH}$	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.49		2.30		3.11		ns
$t_{ESBWEH}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.01		0.35		0.71		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.19		0.62		1.06		ns
$t_{ESBRADDRSU}$	0.25		0.71		1.17		ns
$t_{ESBDATAO1}$		1.01		1.19		1.37	ns
$t_{ESBDATAO2}$		2.18		3.12		4.05	ns
$t_{ESBDD}$		3.19		4.56		5.93	ns
$t_{PD}$		1.57		2.25		2.92	ns
$t_{PTERMSU}$	0.85		1.43		2.01		ns
$t_{PTERMCO}$		1.03		1.21		1.39	ns

**Table 93. EP20K600E  $t_{MAX}$  Routing Delays**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{F1-4}$		0.22		0.25		0.26	ns
$t_{F5-20}$		1.26		1.39		1.52	ns
$t_{F20+}$		3.51		3.88		4.26	ns

Tables 97 through 102 describe  $f_{MAX}$  LE Timing Microparameters,  $f_{MAX}$  ESB Timing Microparameters,  $f_{MAX}$  Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1000E APEX 20KE devices.

**Table 97. EP20K1000E  $f_{MAX}$  LE Timing Microparameters**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{SU}$	0.25		0.25		0.25		ns
$t_H$	0.25		0.25		0.25		ns
$t_{CO}$		0.28		0.32		0.33	ns
$t_{LUT}$		0.80		0.95		1.13	ns

## Version 4.1

*APEX 20K Programmable Logic Device Family Data Sheet* version 4.1 contains the following changes:

- $t_{ESBWEH}$  added to [Figure 37](#) and [Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104](#).
- Updated EP20K300E device internal and external timing numbers in [Tables 79 through 84](#).